# SUD50N03-09P

## Vishay Siliconix



SPECIFICATIONS T <sub>J</sub> = 25 °C Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit	
Static	•,						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA 30				v	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	$V_{DS} = V_{GS}, I_D = 250 \mu A$ 1.0		3.0		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$\begin{tabular}{ c c c c c } \hline $V_{DS} = 30 $ V, $V_{GS} = 0 $ V $ \\ \hline $V_{DS} = 30 $ V, $V_{GS} = 0 $ V, $T_J = 125 $ ^{\circ}C $ \\ \hline \end{tabular}$			1	μA	
					50		
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 10 V$	50			А	
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.0076	0.0095	1	
		$V_{GS}$ = 10 V, $I_{D}$ = 20 A, $T_{J}$ = 125 °C	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C		0.015	Ω	
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		0.0115	0.014	1	
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A	20			S	
Dynamic <sup>a</sup>				•			
Input Capacitance	C <sub>iss</sub>			2200		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS}$ = 0 V, $V_{DS}$ = 25 V, f = 1 MHz		410			
Reverse Transfer Capacitance	C <sub>rss</sub>			180			
Total Gate Charge <sup>c</sup>	Qg			11	16	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 50 \text{ A}$		7.5			
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			5.0			
Gate Resistance	Rg		0.5	1.5	2.1	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			9	15	ns	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 15 V, $R_L$ = 0.3 $\Omega$		15	25		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong$ 50 A, $V_{GEN}$ = 10 V, $R_g$ = 2.5 $\Omega$		22	35		
Fall Time <sup>c</sup>	t <sub>f</sub>			8	12		
Source-Drain Diode Ratings and Cha	racteristic T <sub>C</sub>	2 = 25 °C					
Pulsed Current	I <sub>SM</sub>				100	А	
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	I <sub>F</sub> = 50 A, V <sub>GS</sub> = 0 V		1.2	1.5	V	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 50 A, di/dt = 100 A/μs		35	70	ns	

Notes:

a. Guaranteed by design, not subject to production testing.

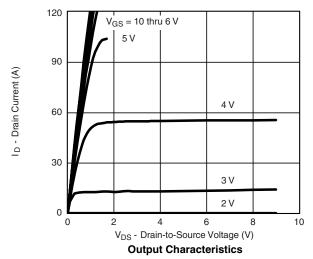
b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

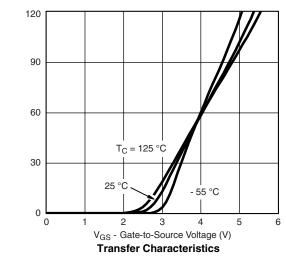
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

I<sub>D</sub> - Drain Current (A)

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





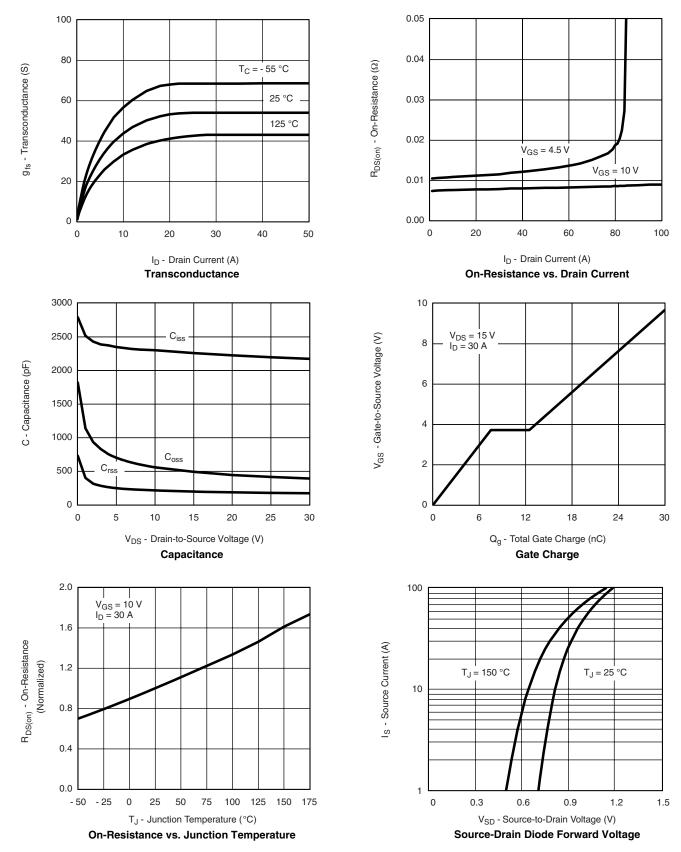
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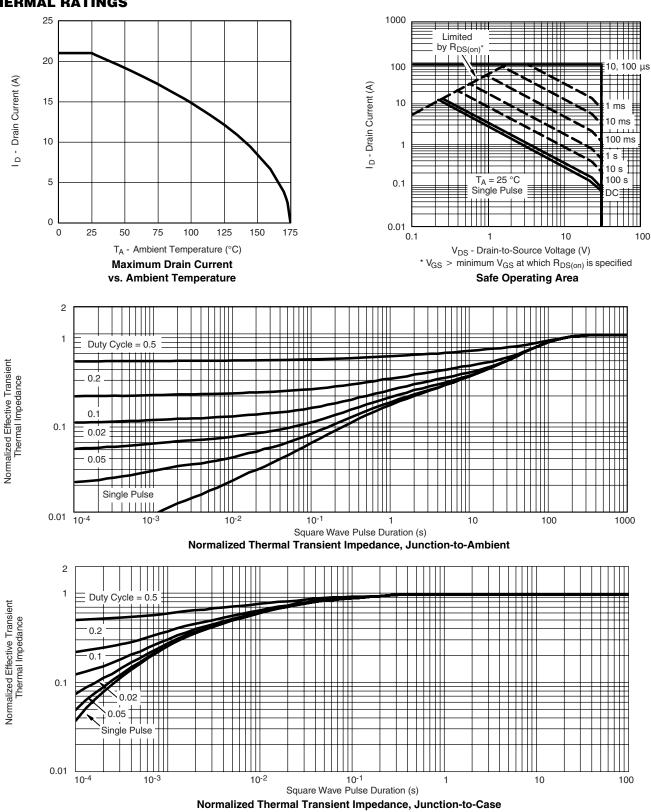


Document Number: 71856 S-80793-Rev. G, 14-Apr-08

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#### THERMAL RATINGS



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?71856.

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Е b3 Ľ Δ ŝ b b2 e1 Б E1 

# C2 т gage plane height (0.5 mm) -C - A1

**TO-252AA Case Outline** 

	MILLIN	IETERS	INCHES				
DIM.	MIN.	MAX.	MIN.	MAX.			
А	2.18	2.38	0.086	0.094			
A1	-	0.127	-	0.005			
b	0.64	0.88	0.025	0.035			
b2	0.76	1.14	0.030	0.045			
b3	4.95	5.46	0.195	0.215			
С	0.46	0.61	0.018	0.024			
C2	0.46	0.89	0.018	0.035			
D	5.97	6.22	0.235	0.245			
D1	4.10	-	0.161	-			
Е	6.35	6.73	0.250	0.265			
E1	4.32	-	0.170	-			
Н	9.40	10.41	0.370	0.410			
е	2.28 BSC		0.090 BSC				
e1	4.56 BSC		0.180 BSC				
L	1.40	1.78	0.055	0.070			
L3	0.89	1.27	0.035	0.050			
L4	-	1.02	-	0.040			
L5	1.01	1.52	0.040	0.060			
ECN: T16-0236-Rev. P, 16-May-16 DWG: 5347							

Notes

• Dimension L3 is for reference only.

Revision: 16-May-16

1 For technical questions, contact: <a href="mailto:pmostechsupport@vishay.com">pmostechsupport@vishay.com</a> Document Number: 71197

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## **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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